Strained Channel Complementary Field-Effect Transistors and Methods of Manufacture

ABSTRACT OF THE DISCLOSURE

A transistor includes a gate dielectric overlying a channel region. A source region and a drain region are located on opposing sides of the channel region. The channel region is formed from a first semiconductor material and the source and drain regions are formed from a second semiconductor material. A gate electrode overlies the gate dielectric. A pair of spacers is formed on sidewalls of the gate electrode. Each of the spacers includes a void adjacent the channel region. A high-stress film can overlie the gate electrode and spacers.

(FIG. 3a)